

## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$ max	$I_D$ max $T_A = +25^\circ\text{C}$
20V	110m $\Omega$ @ $V_{GS} = 4.5\text{V}$	2A
	145m $\Omega$ @ $V_{GS} = 2.5\text{V}$	1.7A
	230m $\Omega$ @ $V_{GS} = 1.8\text{V}$	1.3A

## Description and Applications

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Boost Application
- Analog Switch

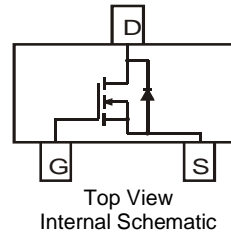


## Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

## Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208  $\text{\textcircled{3}}$
- Weight: 0.008 grams (Approximate)

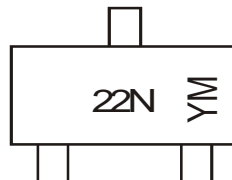


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2230UQ-7	SOT23	3,000/Tape & Reel
DMN2230UQ-13	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/quality/product\\_grade\\_definitions/](http://www.diodes.com/quality/product_grade_definitions/).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



22N = Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: U = 2007)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	U	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	20	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current (Note 6)	I <sub>D</sub>	2.0	A
Pulsed Drain Current (Note 7)	I <sub>DM</sub>	7	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	P <sub>D</sub>	600	mW
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	208	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	—	1.0	V	V <sub>DS</sub> = V <sub>CS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>Ds(on)</sub>	—	81	110	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2.5A
			113	145		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 1.5A
			170	230		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 1.0A
Forward Transfer Admittance	Y <sub>fs</sub>	—	5	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 2.4A
Diode Forward Voltage (Note 8)	V <sub>SD</sub>	—	0.8	1.1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.05A
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	188	—	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	44	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	30	—	pF	
Total Gate Charge	Q <sub>g</sub>	—	2.3	—	nC	V <sub>DS</sub> = 10V, I <sub>D</sub> = 11.6A
Gate-Source Charge	Q <sub>gs</sub>	—	0.3	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	0.5	—	nC	
Turn-On Delay Time	t <sub>d(on)</sub>	—	8	—	ns	V <sub>DD</sub> = 10V, R <sub>L</sub> = 10Ω I <sub>D</sub> = 1A, V <sub>GEN</sub> = 4.5V, R <sub>G</sub> = 6Ω
Rise Time	t <sub>r</sub>	—	3.8	—		
Turn-Off Delay Time	t <sub>d(off)</sub>	—	19.6	—		
Fall Time	t <sub>f</sub>	—	8.3	—		

- Notes:
- Device mounted on FR-4 PCB, or minimum recommended pad layout.
  - Repetitive rating, pulse width limited by junction temperature.
  - Short duration pulse test used to minimize self-heating effect.

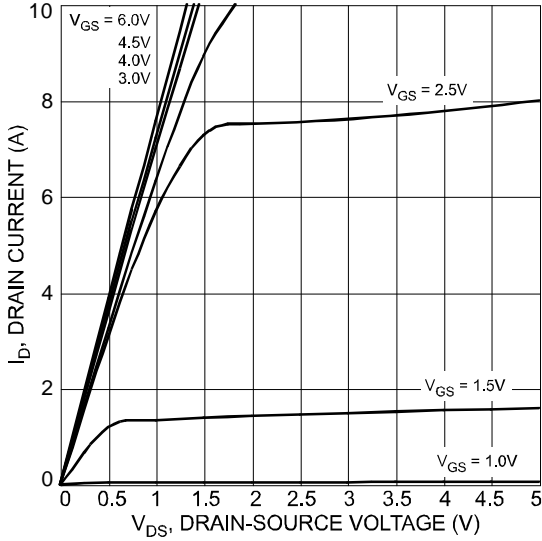


Fig. 1 Typical Output Characteristic

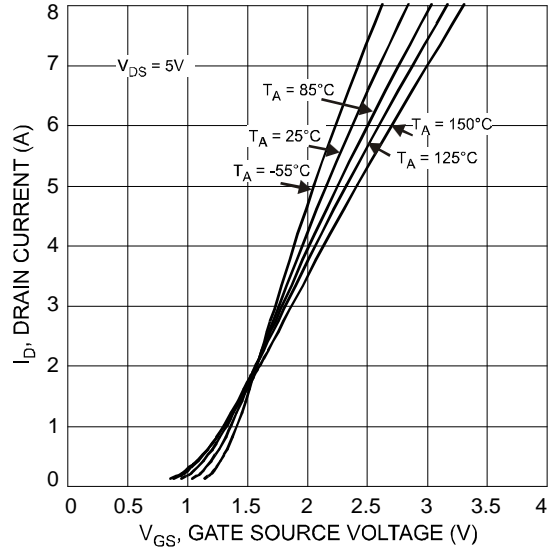


Fig. 2 Typical Transfer Characteristics

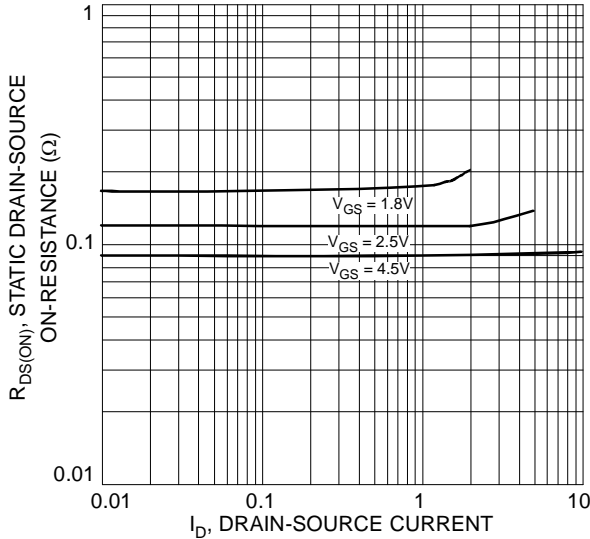


Fig. 3 On-Resistance vs. Drain-Source Current & Gate Voltage

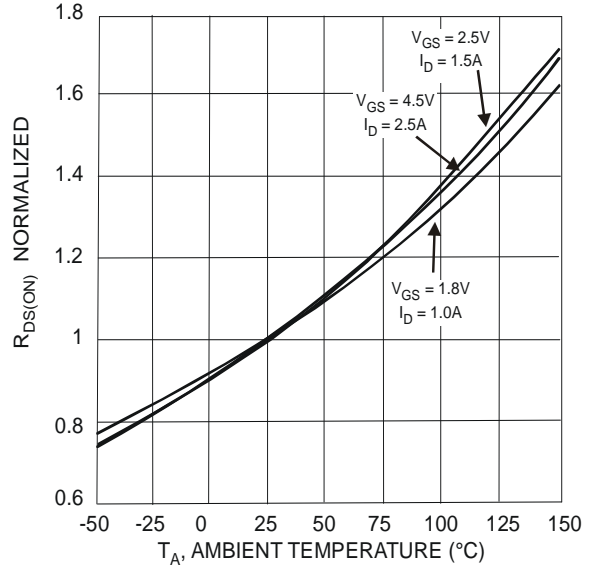


Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

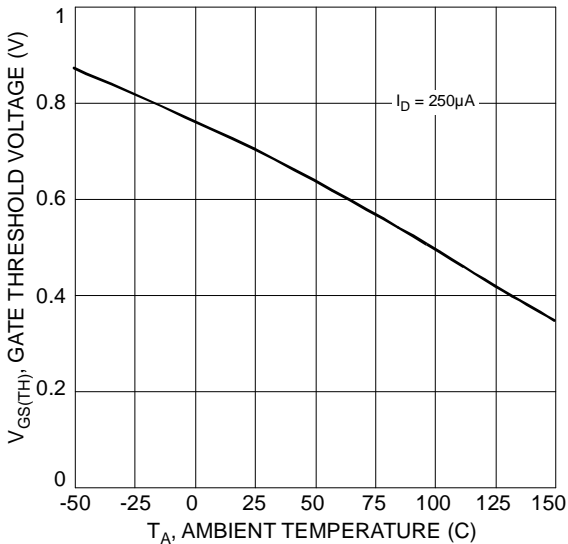


Fig. 5 Gate Threshold Variation with Temperature

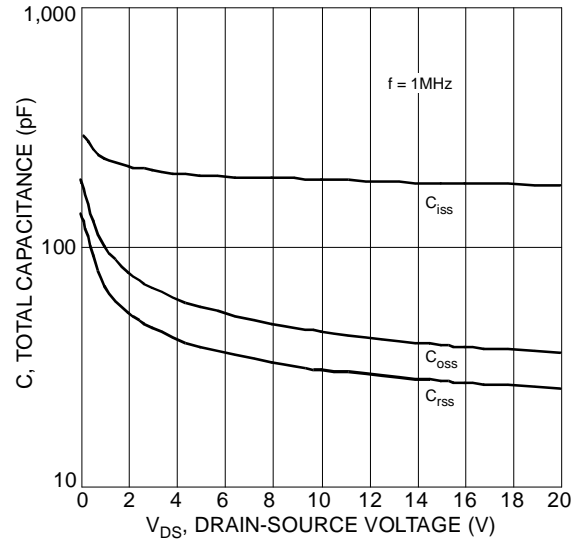


Fig. 6 Typical Total Capacitance

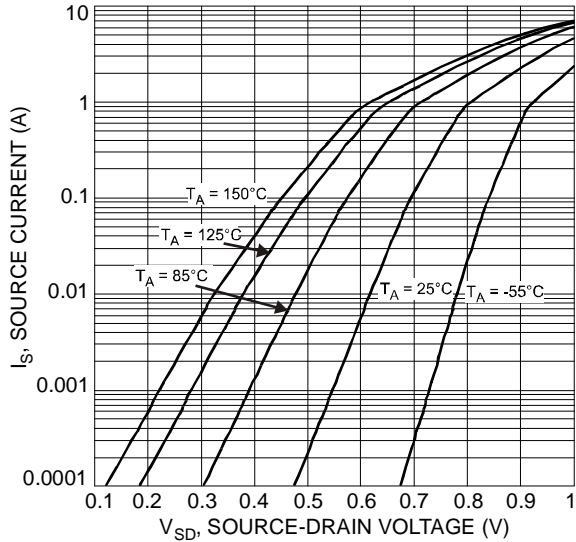


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

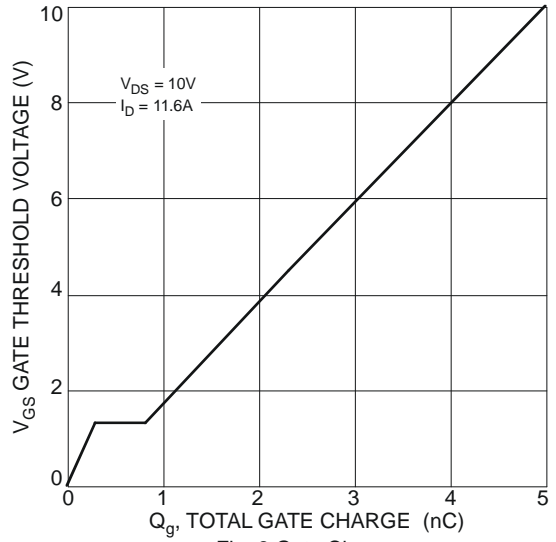


Fig. 8 Gate Charge

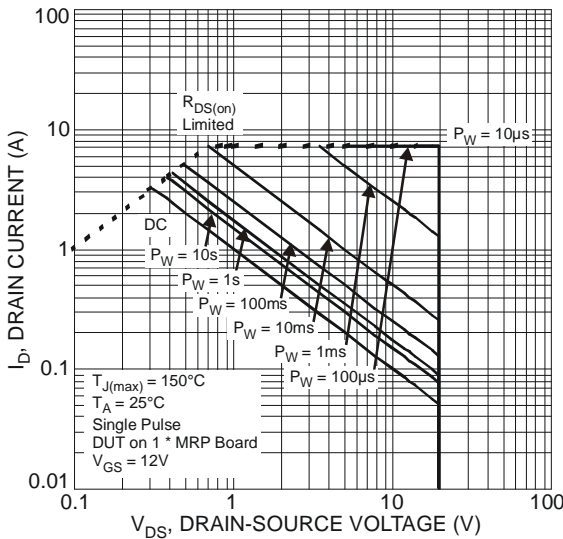
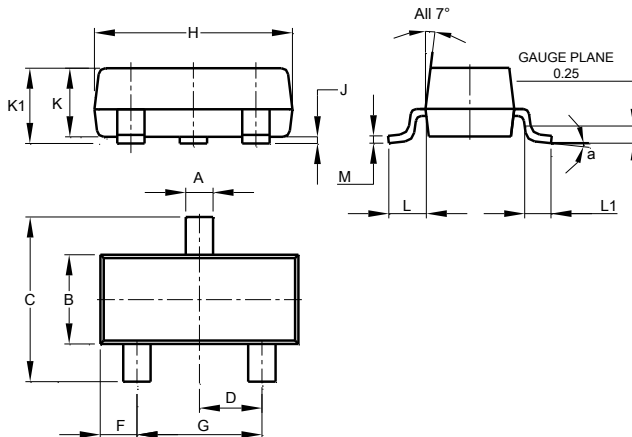


Fig. 9 SOA, Safe Operation Area

**Package Outline Dimensions**

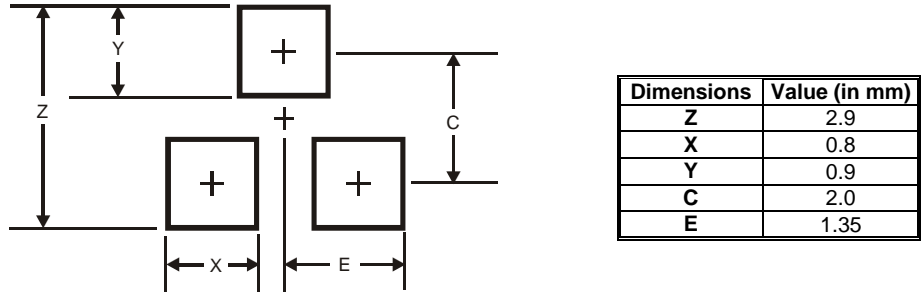
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



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